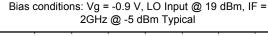
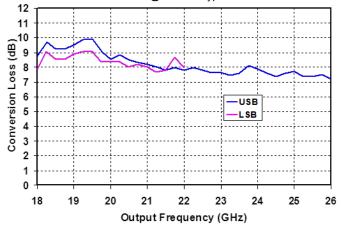


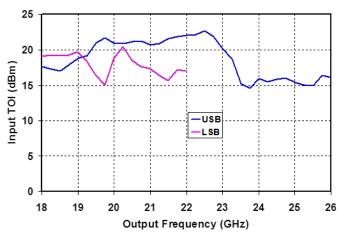
## 18 – 26 GHz Packaged Upconverting Mixer



#### **Measured Performance**







## **Key Features**

RF Output Frequency Range: 18 - 26 GHz

IF Input Frequency Range: 0.5 – 3 GHz

Conversion Loss: 9 dB

• Input TOI: 18 dBm

LO Input Power: 19 dBm

Bias: Vmxr = -0.9 V

Package Dimensions: 4 x 4 x 0.9 mm

## **Primary Applications**

Point-to-Point Radio

K Band Sat-Com

## **Product Description**

The TGC4402-SM upconverting mixer is designed to support a variety of millimeter wave applications including point-to-point digital radio and K band Sat-Com.

The TGC4402-SM provides 9 dB nominal conversion loss across 18-26 GHz . Typical LO input drive is 19 dBm across the band. The input IF Frequency is 0.5-3 GHz.

The TGC4402-SM requires only 2 off-chip components. Each device is 100% DC and RF tested on-wafer to ensure performance compliance. The device is available in chip form.

The TGC4402-SM has a protective surface passivation layer providing environmental robustness.

Lead-free and RoHS compliant

Datasheet subject to change without notice.



### Table I

## **Absolute Maximum Ratings 1/**

Symbol	Parameter	Value	Notes
Vmxr	Gate Supply Voltage Range	-5 - 0 V	
Pin	LO Input Continuous Wave Power	25 dBm	

1/ These ratings represent the maximum operable values for this device. Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device and / or affect device lifetime. These are stress ratings only, and functional operation of the device at these conditions is not implied.

Table II
Recommended Operating Conditions

Symbol	Parameter	Value
Vmxr	Gate Voltage	-0.9 V

# Table III RF Characterization Table

Bias: Vmxr = -0.9 V,  $T_A$  = 25 °C  $\pm$  5°C

		0.0 t, 1 <sub>A</sub> 20 0 <u>-</u> 0 0		
SYMBOL	PARAMETER	TEST CONDITIONS	NOMINAL	UNITS
F <sub>out</sub>	RF Output Frequencies		18 - 26	GHz
F <sub>IF</sub>	IF Input Frequency		0.5 - 3	GHz
F <sub>LO</sub>	LO Input Frequency		16 - 26	GHz
P <sub>LO</sub>	LO Input Power	f = 16 - 26 GHz	19	dBm
	Conversion Loss	f = 18 - 26 GHz	9	dB
ITOI	Input TOI	f = 18 - 26 GHz	18	dBm
	LO – RF Output Isolation	f = 16 - 26 GHz	40	dB
	Conversion Loss Temperature Coefficient	f = 16 - 26 GHz	-0.006	dB / °C





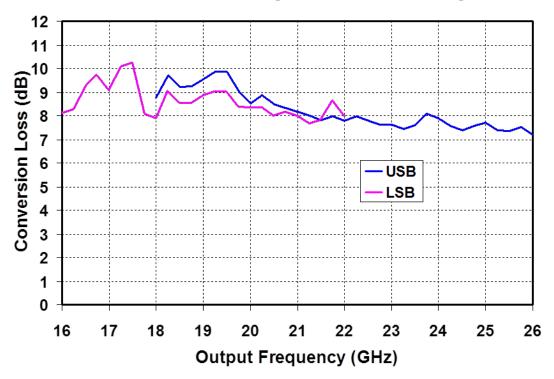
# Table IV Power Dissipation and Thermal Properties

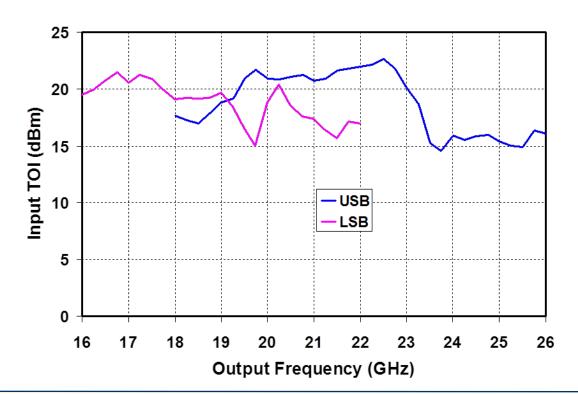
Parameter	Test Conditions	Value	Notes
Maximum Power Dissipation	Tbaseplate = 70 °C	Pd = 0.45 W Tchannel = 138 °C Tm = 1.0E+6 Hrs	1/ 2/
Thermal Resistance, θjc	LO input power is 17 dBm	θjc = 76 (°C/W) Tchannel = 121 °C Tm = >1E+6 Hrs	
Mounting Temperature	30 seconds	320 °C Max	
Storage Temperature		-65 to 150 °C	

- 1/ For a median life, Tm, of 1E+6 hours, power dissipation is limited to  $Pd(max) = (TBD °C Tbase °C)/\theta jc.$
- 2/ Channel operating temperature will directly affect the device median time to failure (MTTF). For maximum life, it is recommended that channel temperatures be maintained at the lowest possible levels.



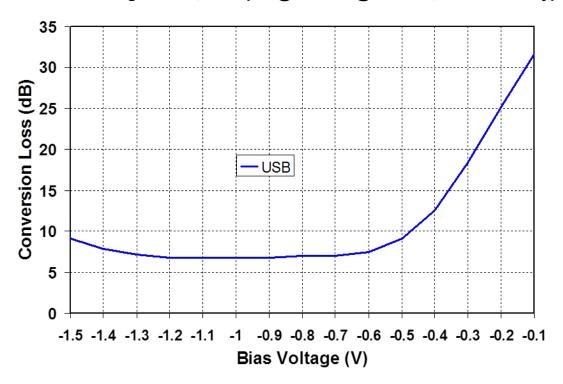
Bias conditions: Vg = -0.9 V, LO Input @ + 19 dBm, IF = 2 GHz @ -5 dBm Typical

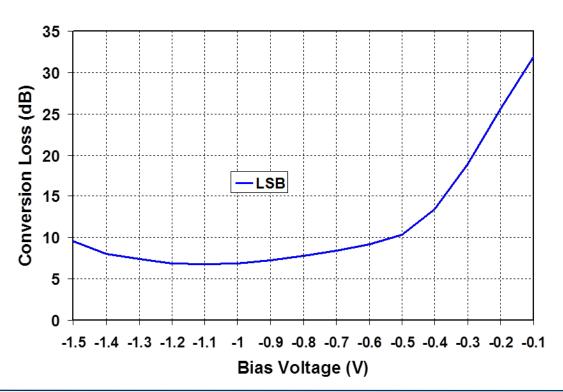






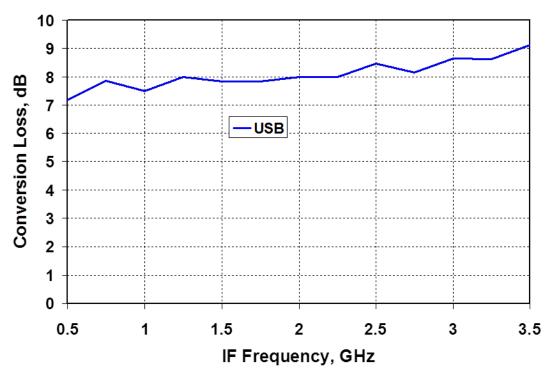
Bias conditions: Vg = -0.9 V, LO Input @ 20 GHz @ 19 dBm, IF = -5 dBm Typical

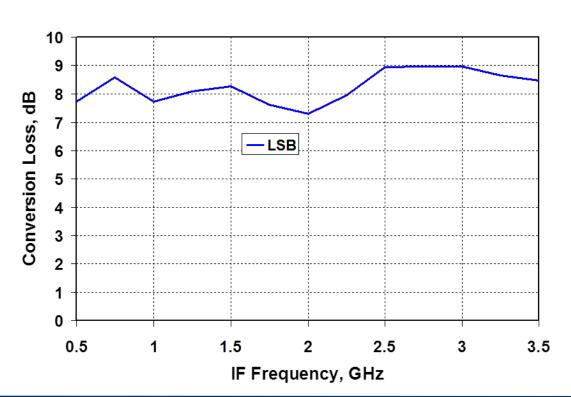






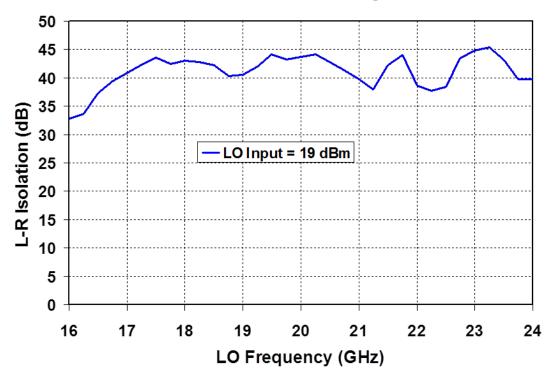








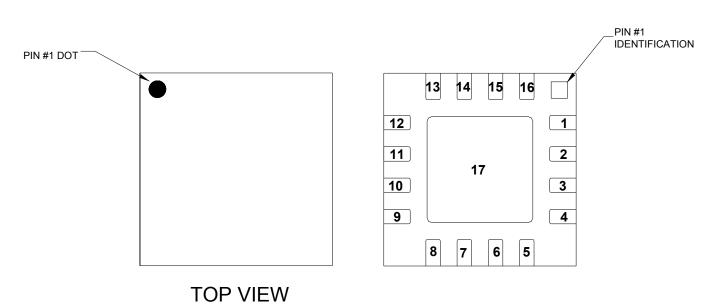








## **Package Pinout**

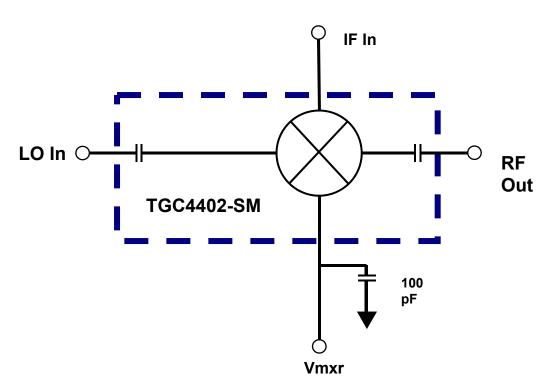


**BOTTOM VIEW** 

Pin	Description
1, 3, 4, 6, 8, 9, 10, 11, 12, 14, 16	N/C
2	IF Input
5, 13	Vmxr
7	LO Input
15	RF Out
17	GND



#### **Electrical Schematic**



## **Bias Procedures**

#### Bias-up Procedure

- Vmxr set to -0.9 V
- Apply signal to IF input
- Apply signal to LO input

#### Bias-down Procedure

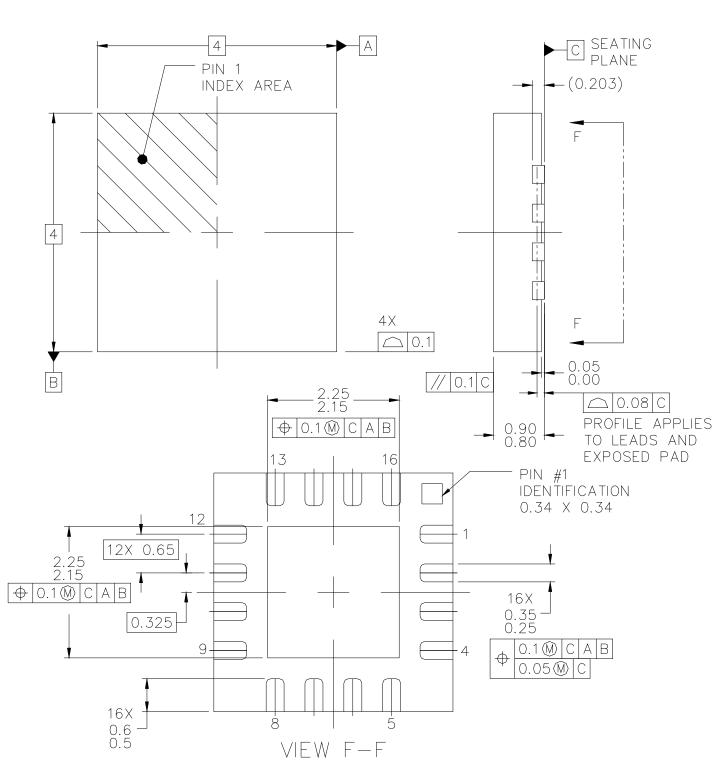
- Turn off IF and LO signals
- Set Vmxr to 0 V



## **Mechanical Drawing**

**Units: Millimeters** 

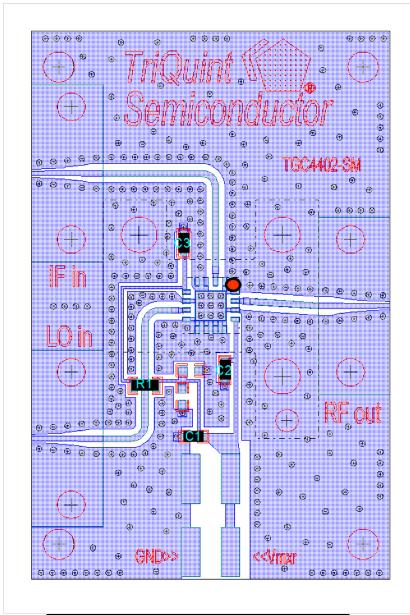
## **TGC4402-SM**



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.



## **Recommended Assembly Diagram**



Part	Description
C1 (optional)	1 uF Capacitor (0402)
C2, C3	100 pF Capacitor (0402)
R1	0 ohm Resistor (0603)

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.



## **Assembly Notes**

Recommended Surface Mount Package Assembly

- Proper ESD precautions must be followed while handling packages.
- Clean the board with acetone. Rinse with alcohol. Allow the circuit to fully dry.
- TriQuint recommends using a conductive solder paste for attachment. Follow solder paste and reflow oven vendors' recommendations when developing a solder reflow profile. Typical solder reflow profiles are listed in the table below.
- Hand soldering is not recommended. Solder paste can be applied using a stencil printer or dot
  placement. The volume of solder paste depends on PCB and component layout and should be well
  controlled to ensure consistent mechanical and electrical performance.
- · Clean the assembly with alcohol.

## **Typical Solder Reflow Profiles**

Reflow Profile	SnPb	Pb Free
Ramp-up Rate	3 °C/sec	3 °C/sec
Activation Time and Temperature	60 – 120 sec @ 140 – 160 °C	60 - 180 sec @ 150 - 200 °C
Time above Melting Point	60 – 150 sec	60 – 150 sec
Max Peak Temperature	240 °C	260 °C
Time within 5 °C of Peak Temperature	10 – 20 sec	10 – 20 sec
Ramp-down Rate	4 – 6 °C/sec	4 – 6 °C/sec

## **Ordering Information**

Part	Package Style
TGC4402-SM	QFN 4x4 Surface Mount

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.